## NSN 5961-01-196-1894

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View Online at https://aerobasegroup.com/nsn/5961-01-196-1894 **Inclosure Material:** Metal **Overall Length:** 0.210 inches **Terminal Length:** 0.500 inches **Overall Diameter:** 0.230 inches **Internal Configuration:** Point contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-18 **Response Time:** 500.0 nanoseconds **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Gallium phosphide Voltage Rating In Volts Per Characteristic: 50.0 collector to base voltage/static/emitter open and 30.0 collector to emitter voltage/static/base open and 7.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 250.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: npn **Precious Material And Location:** External surfaces gold **Precious Material:** Gold **Terminal Type And Quantity:** 3 uninsulated wire lead

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N/a

Shelf Life:

**Unit Of Measure:** 

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Demilitarization:

No

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